



FCPF600N60ZL1

N-Channel SuperFET® II MOSFET

600 V, 7.4 A, 600 mΩ

Features

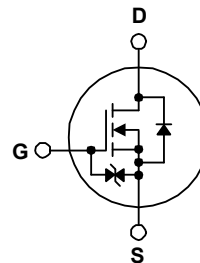
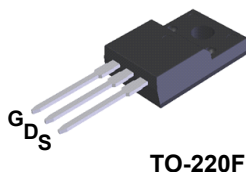
- 650 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 510\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 20\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 74\text{ pF}$)
- 100% Avalanche Tested
- ESD Improved Capacity
- RoHS Compliant

Applications

- LCD / LED TV and Lightning
- Adapter
- AC-DC Power Supply

Description

SuperFET® II MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCPF600N60ZL1	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate to Source Voltage	- DC	± 20 V
		- AC (f > 1 Hz)	± 30 V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	7.4*
		- Continuous ($T_C = 100^\circ\text{C}$)	4.7*
I_{DM}	Drain Current	- Pulsed (Note 1)	22.2*
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	135 mJ
I_{AR}	Avalanche Current	(Note 1)	1.5 A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	0.89 mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	20	
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	28 W
		- Derate Above 25°C	0.22 W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCPF600N60ZL1	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	4.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF600N60ZL1	FCPF600N60Z	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 25^\circ\text{C}$	600	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 150^\circ\text{C}$	650	-	-	
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C	-	0.67	-	$\text{V}/^\circ\text{C}$
BV_{DS}	Drain to Source Avalanche Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 7.4\text{ A}$	-	700	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	-	1.32	-	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 10	μA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.5	-	3.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 3.7\text{ A}$	-	0.51	0.6	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 3.7\text{ A}$	-	6.7	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	840	1120	pF
C_{oss}	Output Capacitance		-	630	840	pF
C_{rss}	Reverse Transfer Capacitance		-	30	45	pF
C_{oss}	Output Capacitance	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	16.5	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$	-	74	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}, I_D = 3.7\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)	-	20	26	nC
Q_{gs}	Gate to Source Gate Charge		-	3.4	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	7.5	-	nC
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	2.89	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 3.7\text{ A}, V_{GS} = 10\text{ V}, R_G = 4.7\text{ }\Omega$ (Note 4)	-	13	36	ns
t_r	Turn-On Rise Time		-	7	24	ns
$t_{d(off)}$	Turn-Off Delay Time		-	39	88	ns
t_f	Turn-Off Fall Time		-	9	28	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current	-	-	7.4	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	22.2	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 3.7 A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 3.7 A, dI _F /dt = 100 A/μs	-	200	-	ns
Q _{rr}	Reverse Recovery Charge		-	2.3	-	μC

Notes:

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. $I_{AS} = 1.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 3.7\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

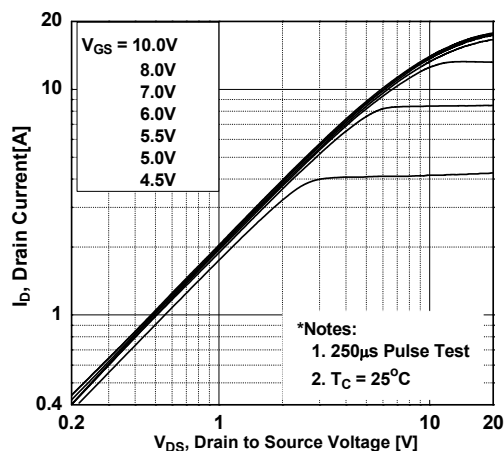


Figure 2. Transfer Characteristics

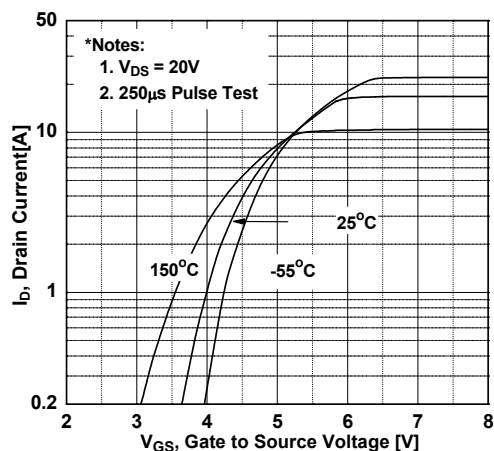


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

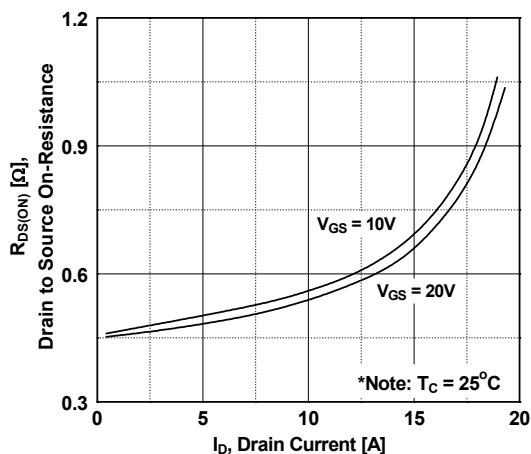


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

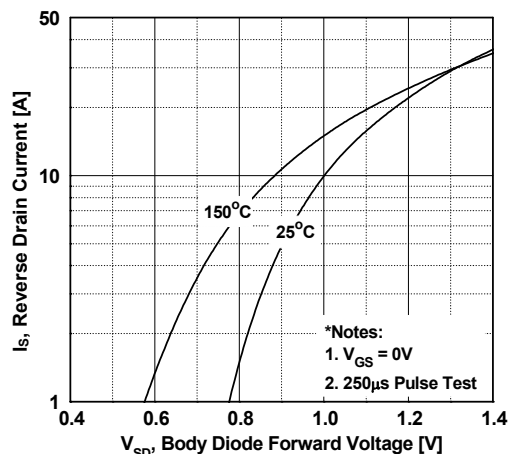


Figure 5. Capacitance Characteristics

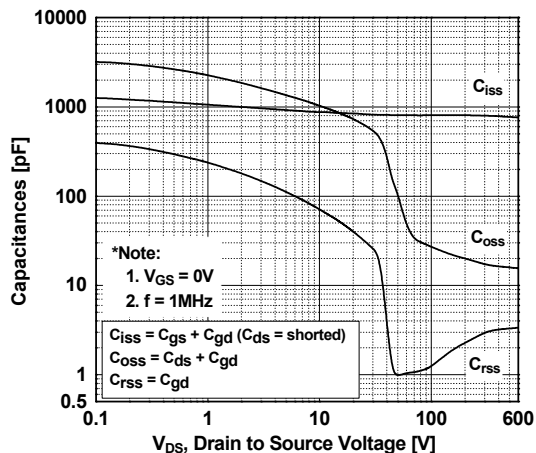
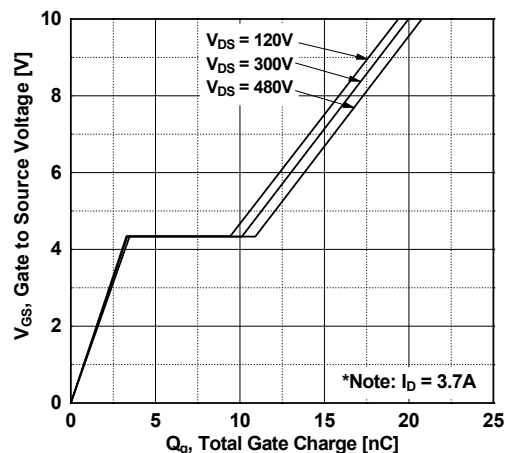


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

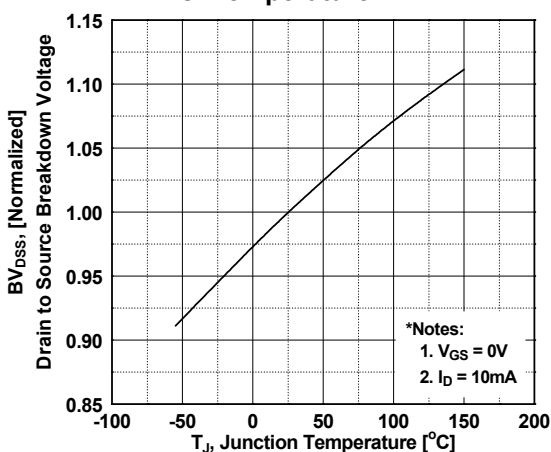


Figure 8. On-Resistance Variation vs. Temperature

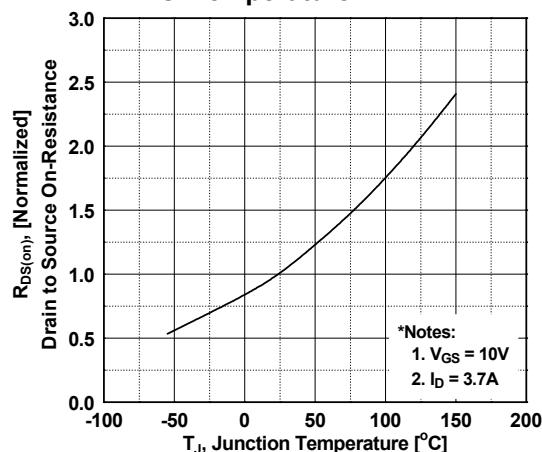


Figure 9. Maximum Safe Operating Area

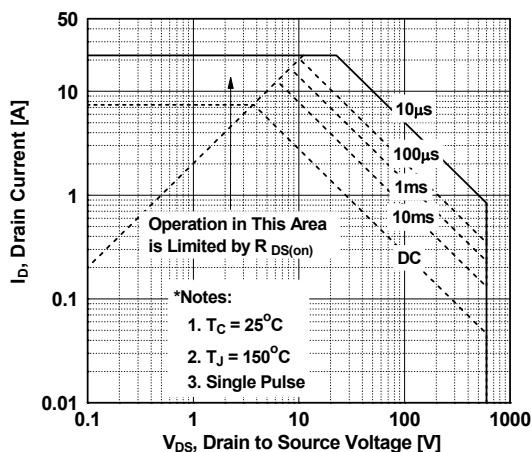


Figure 10. Maximum Drain Current vs. Case Temperature

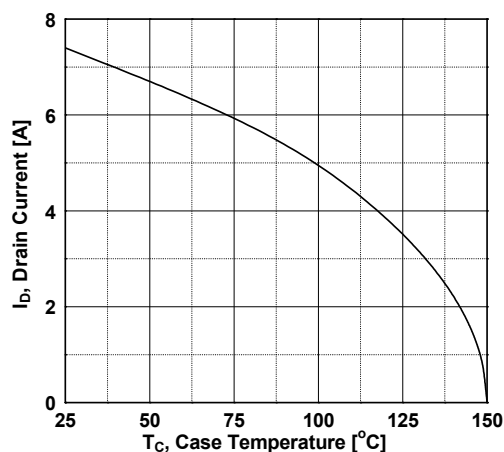
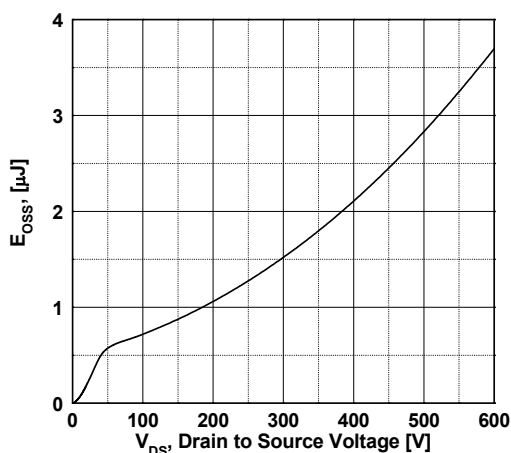
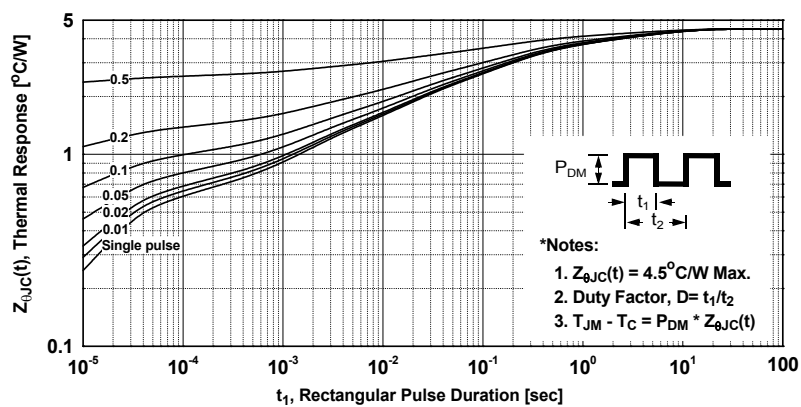


Figure 11. Eoss vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



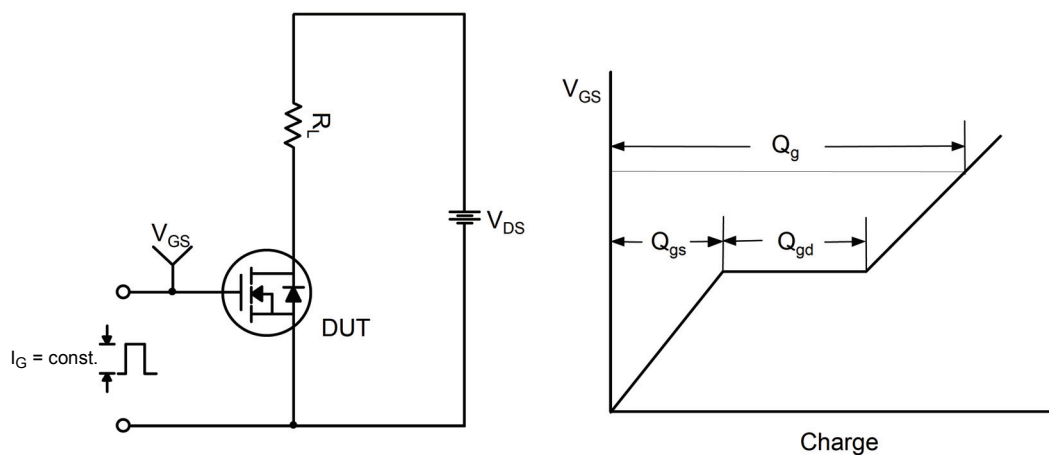


Figure 13. Gate Charge Test Circuit & Waveform

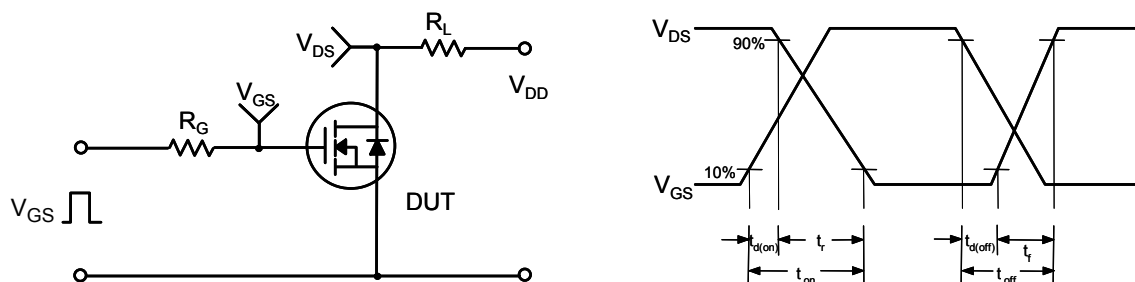


Figure 14. Resistive Switching Test Circuit & Waveforms

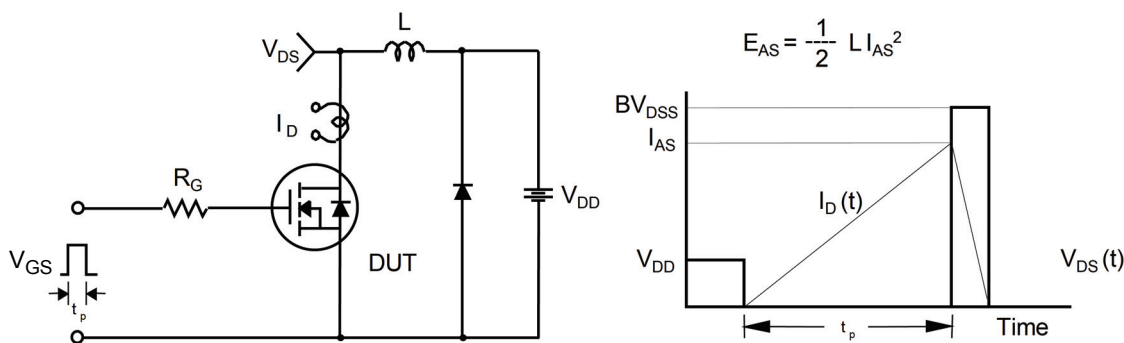


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

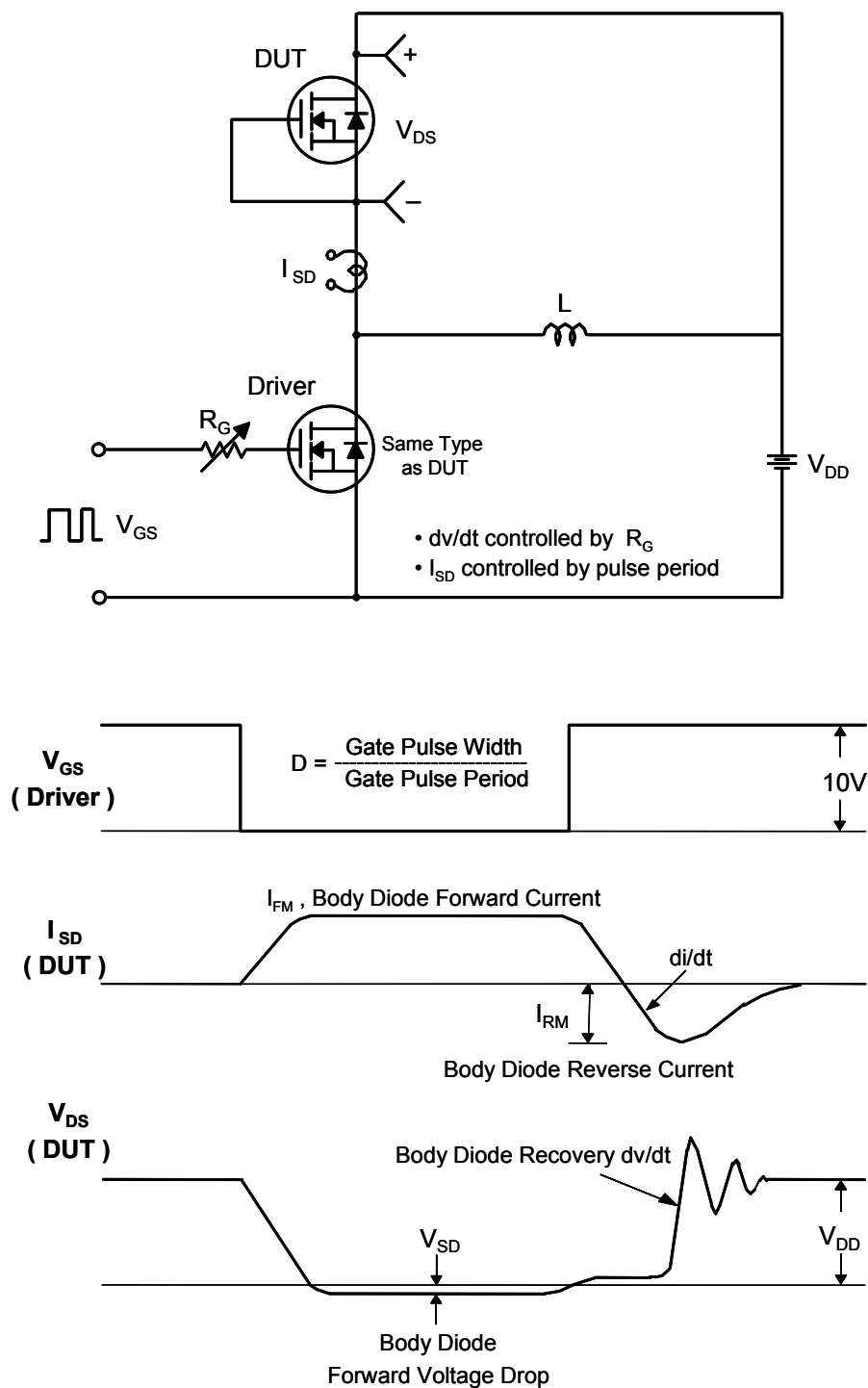
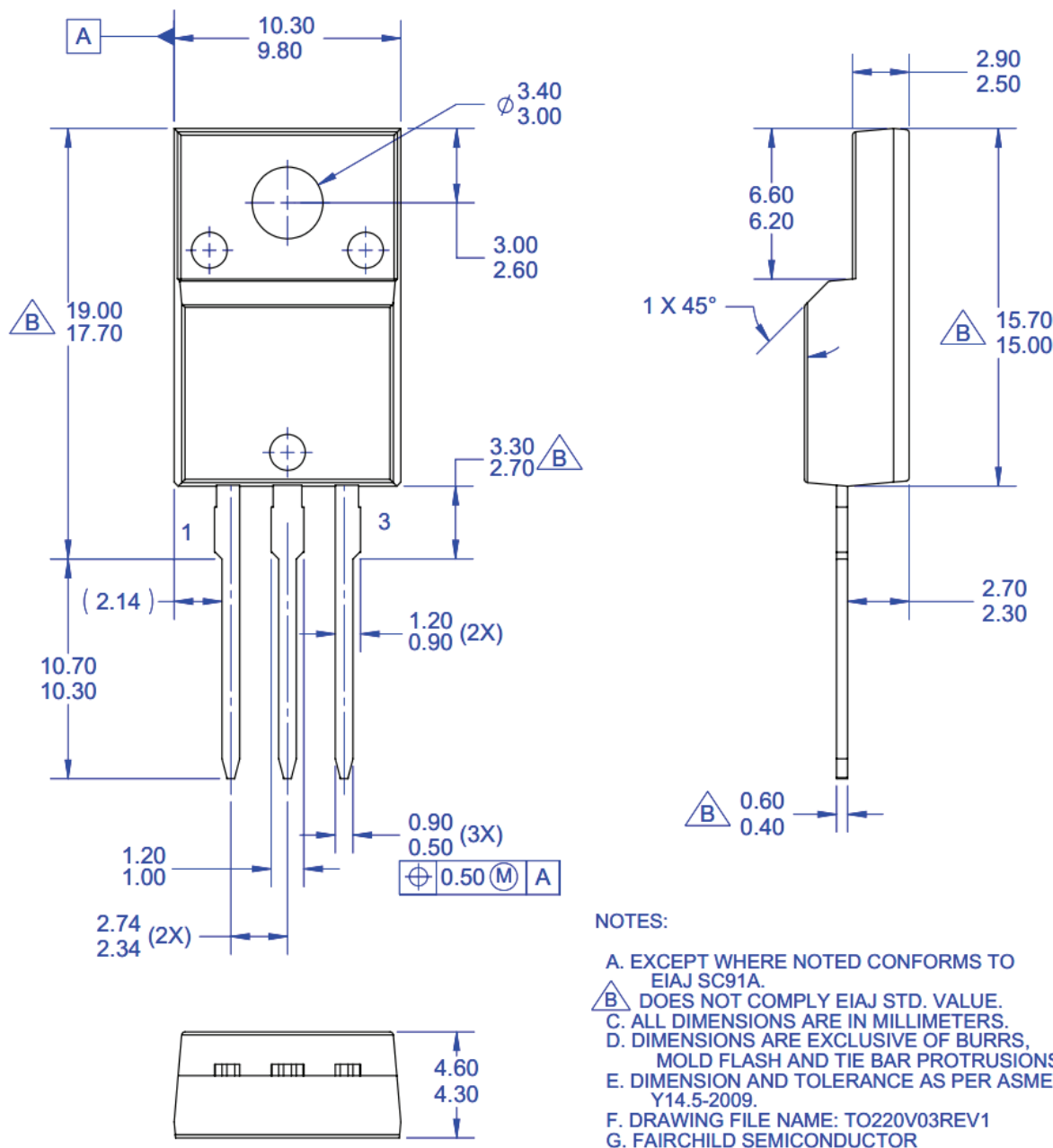


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



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